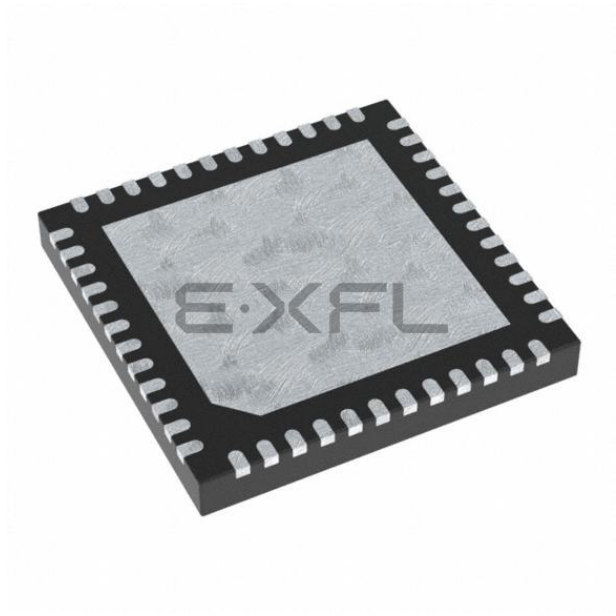

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	27
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.68V ~ 3.6V
Data Converters	A/D 3x12b; D/A 1x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/atsam4lc4aa-mur

Table 2-2. ATSAM4LC Configuration Summary

Feature	ATSAM4LC8/4/2C	ATSAM4LC8/4/2B	ATSAM4LC8/4/2A
Oscillators	Digital Frequency Locked Loop 20-150MHz (DFLL) Phase Locked Loop 48-240MHz (PLL) Crystal Oscillator 0.6-30MHz (OSC0) Crystal Oscillator 32kHz (OSC32K) RC Oscillator 80MHz (RC80M) RC Oscillator 4,8,12MHz (RCFAST) RC Oscillator 115kHz (RCSYS) RC Oscillator 32kHz (RC32K)		
ADC	15-channel	7-channel	3-channel
DAC	1-channel		
Analog Comparators	4	2	1
CATB Sensors	32	32	26
USB	1		
Audio Bitstream DAC	1		
IIS Controller	1		
Packages	TQFP/VFBGA	TQFP/QFN/ WLCSP	TQFP/QFN

.

Table 2-3. ATSAM4LS Configuration Summary

Feature	ATSAM4LS8/4/2C	ATSAM4LS8/4/2B	ATSAM4LS8/4/2A
Number of Pins	100	64	48
Max Frequency	48MHz		
Flash	512/256/128KB		
SRAM	64/32/32KB		
SEGMENT LCD	NA		
GPIO	80	48	32
High-drive pins	6	3	1
External Interrupts	8 + 1 NMI		
TWI	2 Masters + 2 Masters/Slaves		1 Master + 1 Master/Slave
USART	4		3 in LC sub series 4 in LS sub series
PICOUART	1		0
Peripheral DMA Channels	16		
AESA	NA		
Peripheral Event System	1		
SPI	1		
Asynchronous Timers	1		

Table 3-8. Signal Descriptions List (Sheet 4 of 4)

Signal Name	Function	Type	Active Level	Comments
PA31 - PA00	Parallel I/O Controller I/O Port A	I/O		
PB15 - PB00	Parallel I/O Controller I/O Port B	I/O		
PC31 - PC00	Parallel I/O Controller I/O Port C	I/O		

Note: 1. See "Power and Startup Considerations" section.

3.4 I/O Line Considerations

3.4.1 SW/JTAG Pins

The JTAG pins switch to the JTAG functions if a rising edge is detected on TCK low after the RESET_N pin has been released. The TMS, and TDI pins have pull-up resistors when used as JTAG pins. The TCK pin always has pull-up enabled during reset. The JTAG pins can be used as GPIO pins and multiplexed with peripherals when the JTAG is disabled. Refer to Section 3.2.3 "JTAG Port Connections" on page 29 for the JTAG port connections.

For more details, refer to Section 1.1 "Enhanced Debug Port (EDP)" on page 3.

3.4.2 RESET_N Pin

The RESET_N pin is a schmitt input and integrates a permanent pull-up resistor to VDDIN. As the product integrates a power-on reset detector, the RESET_N pin can be left unconnected in case no reset from the system needs to be applied to the product.

3.4.3 TWI Pins

When these pins are used for TWI, the pins are open-drain outputs with slew-rate limitation and-inputs with inputs with spike-filtering. When used as GPIO-pins or used for other peripherals, the pins have the same characteristics as GPIO pins.

3.4.4 GPIO Pins

All the I/O lines integrate a pull-up/pull-down resistor and slew rate controller. Programming these features is performed independently for each I/O line through the GPIO Controllers. After reset, I/O lines default as inputs with pull-up and pull-down resistors disabled and slew rate enabled.

3.4.5 High-drive Pins

The six pins PA02, PB00, PB01, PC04, PC05 and PC06 have high-drive output capabilities. Refer to Section 9.6.2 "High-drive I/O Pin : PA02, PC04, PC05, PC06" on page 115 for electrical characteristics.

3.4.6 USB Pins

When these pins are used for USB, the pins are behaving according to the USB specification. When used as GPIO pins or used for other peripherals, the pins have the same behavior as other normal I/O pins, but the characteristics are different. Refer to Section 9.6.3 "USB I/O Pin : PA25, PA26" on page 116 for electrical characteristics.

These pins are compliant to USB standard only when VDDIO power supply is 3.3V nominal.

4.4 Cortex-M4 processor features and benefits summary

- **tight integration of system peripherals reduces area and development costs**
- **Thumb instruction set combines high code density with 32-bit performance**
- **code-patch ability for ROM system updates**
- **power control optimization of system components**
- **integrated sleep modes for low power consumption**
- **fast code execution permits slower processor clock or increases sleep mode time**
- **hardware division and fast digital-signal-processing orientated multiply accumulate**
- **saturating arithmetic for signal processing**
- **deterministic, high-performance interrupt handling for time-critical applications**
- ***memory protection unit* (MPU) for safety-critical applications**
- **extensive debug and trace capabilities:**
  - **Serial Wire Debug and Serial Wire Trace reduce the number of pins required for debugging, tracing, and code profiling.**

4.5 Cortex-M4 core peripherals

These are:

Nested Vectored Interrupt Controller

The NVIC is an embedded interrupt controller that supports low latency interrupt processing.

System control block

The *System control block* (SCB) is the programmers model interface to the processor. It provides system implementation information and system control, including configuration, control, and reporting of system exceptions.

System timer

The system timer, SysTick, is a 24-bit count-down timer. Use this as a Real Time Operating System (RTOS) tick timer or as a simple counter.

Memory protection unit

The *Memory protection unit* (MPU) improves system reliability by defining the memory attributes for different memory regions. It provides up to eight different regions, and an optional predefined background region.

The complete Cortex-M4 User Guide can be found on the ARM web site:

http://infocenter.arm.com/help/topic/com.arm.doc.dui0553a/DUI0553A_cortex_m4_dgug.pdf

7.1.3 BACKUP Mode

The BACKUP mode allows achieving the lowest power consumption possible in a system which is performing periodic wake-ups to perform tasks but not requiring fast startup time.

The Core domain is powered-off. The internal SRAM and register contents of the Core domain are lost. The Backup domain is kept powered-on. The 32kHz clock (RC32K or OSC32K) is kept running if enabled to feed modules that require clocking.

In BACKUP mode, the configuration of the I/O lines is preserved. Refer to Section 9. ”Backup Power Manager (BPM)” on page 677 to have more details.

7.1.3.1 Entering BACKUP Mode

The Backup mode is entered by using the WFI instruction with the following settings:

- set the SCR.SLEEPDEEP bit to 1. (See the Power Management section in the ARM Cortex-M4 Processor chapter).
- set the BPM.PSAVE.BKUP bit to 1.

7.1.3.2 Exiting BACKUP Mode

Exit from BACKUP mode happens if a reset occurs or if an enabled wake up event occurs.

The reset sources are:

- BOD33 reset
- BOD18 reset
- WDT reset
- External reset in RESET_N pin

The wake up sources are:

- EIC lines (level transition only)
- BOD33 interrupt
- BOD18 interrupt
- AST alarm, periodic, overflow
- WDT interrupt

The RC32K or OSC32K should be used as clock source for modules if required. The PMCON.CK32S is used to select one of these two 32kHz clock sources.

Exiting the BACKUP mode is triggered by:

- a reset source: an internal reset sequence is performed according to the reset source. Once VDDCORE is stable and has the correct value according to RUN0 mode, the internal reset is released and program execution starts. The corresponding reset source is flagged in the Reset Cause register (RCAUSE) of the PM.
- a wake up source: the Backup domain is not reset. An internal reset is generated to the Core domain, and the system switches back to the previous RUN mode. Once VDDCORE is stable and has the correct value, the internal reset in the Core domain is released and program execution starts. The BKUP bit is set in the Reset Cause register (RCAUSE) of the PM. It allows the user to discriminate between the reset cause and a wake up cause from the BACKUP mode. The wake up cause can be found in the Backup Wake up Cause register (BPM.BKUPWCAUSE).

7.1.4 Wakeup Time

7.1.4.1 Wakeup Time From SLEEP Mode

The latency depends on the clock sources wake up time. If the clock sources are not stopped, there is no latency to wake the clocks up.

7.1.4.2 Wakeup Time From WAIT or RETENTION Mode

The wake up latency consists of:

- the switching time from the low power configuration to the RUN mode power configuration. By default, the switching time is completed when all the voltage regulation system is ready. To speed-up the startup time, the user can set the Fast Wakeup bit in BPM.PMCON register.
- the wake up time of the RC oscillator used to start the system up. By default, the RCSYS oscillator is used to startup the system. The user can use another clock source (RCFAST for example) to speed up the startup time by configuring the PM.FASTWKUP register. Refer to Section 9. ”Power Manager (PM)” on page 677.
- the Flash memory wake up time.

To have the shortest wakeup time, the user should:

- set the BPM.PMCON.FASTWKUP bit.

- configure the PM.FASTSLEEP.FASTRCOSC field to use the RCFAST main clock.

- enter the WAIT or RETENTION mode

Upon a wakeup, this is required to keep the main clock connected to RCFAST until the voltage regulation system is fully ready (when BPM.ISR.PSOK bit is one). During this wakeup period, the FLASHCALW module is automatically configured to operate in “1 wait state mode”.

7.1.4.3 Wake time from BACKUP mode

It is equal to the Core domain logic reset latency (similar to the reset latency caused by an external reset in RESET_N pin) added to the time required for the voltage regulation system to be stabilized.

8.7.12 JTAG Instructions Summary

The implemented JTAG instructions are shown in the table below.

Table 8-2. Implemented JTAG instructions list

IR instruction value	Instruction	Description	availability when protected	Component
b0000	EXTEST	Select boundary-scan chain as data register for testing circuitry external to the device.	yes	BSCAN-TAP
b0001	SAMPLE_PRELOAD	Take a snapshot of external pin values without affecting system operation.	yes	
b0100	INTEST	Select boundary-scan chain for internal testing of the device.	yes	
b0101	CLAMP	Bypass device through Bypass register, while driving outputs from boundary-scan register.	yes	
b1000	ABORT	ARM JTAG-DP Instruction	yes	SWJ-DP (in JTAG mode)
b1010	DPACC	ARM JTAG-DP Instruction	yes	
b1011	APACC	ARM JTAG-DP Instruction	yes	
b1100	-	Reserved	yes	
b1101	-	Reserved	yes	
b1110	IDCODE	ARM JTAG-DP Instruction	yes	
b1111	BYPASS	Bypass this device through the bypass register.	yes	

8.9.11.1 Control Register

Name: CR

Access Type: Write-Only

Offset: 0x00

Reset Value: 0x00000000

31	30	29	28	27	26	25	24
-	-	-	-	-	-	-	-

23	22	21	20	19	18	17	16
-	-	-	-	-	-	-	-

15	14	13	12	11	10	9	8
-	-	-	-	-	-	-	-

7	6	5	4	3	2	1	0
-	-	-	CE	FSPR	CRC	DIS	EN

Writing a zero to a bit in this register has no effect.

- **CE: Chip Erase**
  Writing a one to this bit triggers the FLASH Erase All (EA) operation which clears all volatile memories, the whole flash array, the general purpose fuses and the protected state. The Status register DONE field indicates the completion of the operation.
  Reading this bit always returns 0
- **FSPR: Flash User Page Read**
  Writing a one to this bit triggers a read operation in the User page. The word pointed by the ADDR register in the page is read and written to the DATA register. ADDR is post incremented allowing a burst of reads without modifying ADDR. SR.DONE must be read high prior to reading the DATA register.
  Reading this bit always returns 0
- **CRC: Cyclic Redundancy Code**
  Writing a one triggers a CRC calculation over a memory area defined by the ADDR and LENGTH registers. Reading this bit always returns 0
  Note: This feature is restricted while in protected state
- **DIS: Disable**
  Writing a one to this bit disables the module. Disabling the module resets the whole module immediately.
- **EN: Enable**
  Writing a one to this bit enables the module.

0: No bus error has been detected sincle last clear of this bit

- **HCR: Hold Core reset**
  1: The Cortex-M4 core is held under reset
  0: The Cortex-M4 core is not held under reset
- **DONE: Operation done**
  1: At least one operation has terminated since last clear of this field
  0: No operation has terminated since last clear of this field

8.9.11.6 Data Register

Name: DATA

Access Type: Read/Write

Offset: 0x14

Reset Value: 0x00000000

31	30	29	28	27	26	25	24
DATA							

23	22	21	20	19	18	17	16
DATA							

15	14	13	12	11	10	9	8
DATA							

7	6	5	4	3	2	1	0
DATA							

- **DATA: Generic data register**

8.9.11.7 Module Version

Name: VERSION

Access Type: Read-Only

Offset: 0x28

Reset Value: -

31	30	29	28	27	26	25	24
-	-	-	-	-	-	-	-

23	22	21	20	19	18	17	16
-	-	-	-	VARIANT			

15	14	13	12	11	10	9	8
-	-	-	-	VERSION			

7	6	5	4	3	2	1	0
VERSION							

- **VARIANT: Variant number**
  Reserved. No functionality associated.
- **VERSION: Version number**
  Version number of the module. No functionality associated.

3. These values are based on characterization. These values are not covered by test limits in production

9.6.2 High-drive I/O Pin : PA02, PC04, PC05, PC06

Table 9-14. High-drive I/O Pin Characteristics (1)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
R_{PULLUP}	Pull-up resistance (2)				40		kΩ
$R_{PULLDOWN}$	Pull-down resistance(2)				40		kΩ
V_{IL}	Input low-level voltage			-0.3		0.2 * V_{VDD}	V
V_{IH}	Input high-level voltage			0.8 * V_{VDD}		V_{VDD} + 0.3	
V_{OL}	Output low-level voltage					0.4	
V_{OH}	Output high-level voltage			V_{VDD} - 0.4			
I_{OL}	Output low-level current (3)	ODCR0=0	1.68V<V_{VDD}<2.7V			1.8	mA
			2.7V<V_{VDD}<3.6V			3.2	
		ODCR0=1	1.68V<V_{VDD}<2.7V			3.2	mA
			2.7V<V_{VDD}<3.6V			6	
I_{OH}	Output high-level current(3)	ODCR0=0	1.68V<V_{VDD}<2.7V			1.6	mA
			2.7V<V_{VDD}<3.6V			3.2	
		ODCR0=1	1.68V<V_{VDD}<2.7V			3.2	mA
			2.7V<V_{VDD}<3.6V			6	
t_{RISE}	Rise time(2)	OSRR0=0	ODCR0=0 1.68V<V_{VDD}<2.7V, Cload = 25pF			20	ns
		OSRR0=1				40	
		OSRR0=0	ODCR0=0 2.7V<V_{VDD}<3.6V, Cload = 25pF			11	ns
		OSRR0=1				18	
t_{FALL}	Fall time(2)	OSRR0=0	ODCR0=0 1.68V<V_{VDD}<2.7V, Cload = 25pF			20	ns
		OSRR0=1				40	
		OSRR0=0	ODCR0=0 2.7V<V_{VDD}<3.6V, Cload = 25pF			11	ns
		OSRR0=1				18	
F_{PINMAX}	Output frequency(2)	OSRR0=0	ODCR0=0, V_{VDD}>2.7V load = 25pF			22	MHz
		OSRR0=1				17	MHz
		OSRR0=0	ODCR0=1, V_{VDD}>2.7V load = 25pF			35	MHz
		OSRR0=1				26	MHz
I_{LEAK}	Input leakage current(3)	Pull-up resistors disabled			0.01	2	µA
C_{IN}	Input capacitance(2)				10		pF

1. V_{VDD} corresponds to either V_{VDDIN} or V_{VDDIO}, depending on the supply for the pin. Refer to Section 3-5 on page 13 for details
2. These values are based on simulation. These values are not covered by test limits in production or characterization
3. These values are based on characterization. These values are not covered by test limits in production

9.6.5 High Drive TWI Pin : PB00, PB01

Table 9-19. High Drive TWI Pin Characteristics in TWI configuration (1)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
R_{PULLUP}	Pull-up resistance (2)	PB00, PB01			40		kΩ
$R_{PULLDOWN}$	Pull-down resistance(2)				40		kΩ
V_{IL}	Input low-level voltage			-0.3		0.3 * V_{VDD}	V
V_{IH}	Input high-level voltage			0.7 * V_{VDD}		V_{VDD} + 0.3	
V_{OL}	Output low-level voltage					0.4	
V_{OH}	Output high-level voltage			V_{VDD} - 0.4			
I_{OL}	Output low-level current (3)	DRIVEL=0				0.5	mA
		DRIVEL=1				1.0	
		DRIVEL=2				1.6	
		DRIVEL=3				3.1	
		DRIVEL=4				6.2	
		DRIVEL=5				9.3	
		DRIVEL=6				15.5	
		DRIVEL=7				21.8	
I_{CS}	Current Source(2)	DRIVEH=0			0.5		mA
		DRIVEH=1			1		
		DRIVEH=2			1.5		
		DRIVEH=3			3		
f_{MAX}	Max frequency(2)	HsMode with Current source; DRIVEx=3, SLEW=0 Cbus = 400pF, V_{VDD} = 1.68V		3.5	6.4		MHz
t_{RISE}	Rise time(2)	HsMode Mode, DRIVEx=3, SLEW=0 Cbus = 400pF, Rp = 440Ohm, V_{VDD} = 1.68V			28	38	ns
t_{FALL}	Fall time(2)	Standard Mode, DRIVEx=3, SLEW=0 Cbus = 400pF, Rp = 440Ohm, V_{VDD} = 1.68V			50	95	ns
		HsMode Mode, DRIVEx=3, SLEW=0 Cbus = 400pF, Rp = 440Ohm, V_{VDD} = 1.68V			50	95	

1. V_{VDD} corresponds to either V_{VDDIN} or V_{VDDIO}, depending on the supply for the pin. Refer to Section 3-5 on page 13 for details
2. These values are based on simulation. These values are not covered by test limits in production or characterization
3. These values are based on characterization. These values are not covered by test limits in production

9.9.7 Liquid Crystal Display Controler characteristics

Table 9-51. Liquid Crystal Display Controler characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Units
SEG	Segment Terminal Pins				40	
COM	Common Terminal Pins				4	
f_{Frame}	LCD Frame Frequency	F_{CLKLCD}	31.25		512	Hz
C_{Flying}	Flying Capacitor			100		nF
V_{LCD}	LCD Regulated Voltages (1) CFG.FCST=0	C_{Flying} = 100nF 100nF on V_{LCD}, BIAS2 and BIAS1 pins		3		V
BIAS2				$2*V_{LCD}/3$		
BIAS1				$V_{LCD}/3$		

1. These values are based on simulation. These values are not covered by test limits in production or characterization

9.9.7.1 Liquid Crystal Controler supply current

The values in Table 9-52 are measured values of power consumption under the following conditions, except where noted:

- T=25°C, WAIT mode, Low power waveform, Frame Rate = 32Hz from OSC32K
- Configuration: 4COMx40SEG, 1/4 Duty, 1/3 Bias, No animation
- All segments on, Load = 160 x 22pF between each COM and each SEG.
- LCDCA current based on $I_{LCD} = I_{WAIT}$(Lcd On) - I_{WAIT}(Lcd Off)

Table 9-52. Liquid Crystal Display Controler supply current

Symbol	Conditions		Min	Typ	Max	Units
I_{LCD}	Internal voltage generation CFG.FCST=0	V_{VDDIN} = 3.6V		8.85		µA
		V_{VDDIN} = 1.8V		6.16		
	External bias V_{LCD}=3.0V	V_{VDDIN} = 3.3V		0.98		
		V_{VDDIN} = 1.8V		1.17		

9.10 Timing Characteristics

9.10.1 RESET_N Timing

Table 9-53. RESET_N Waveform Parameters [1]

Symbol	Parameter	Conditions	Min	Max	Units
t_{RESET}	RESET_N minimum pulse length		10		ns

1. These values are based on simulation. These values are not covered by test limits in production.

9.10.2 USART in SPI Mode Timing

9.10.2.1 Master mode

Figure 9-7. USART in SPI Master Mode with (CPOL= CPHA= 0) or (CPOL= CPHA= 1)

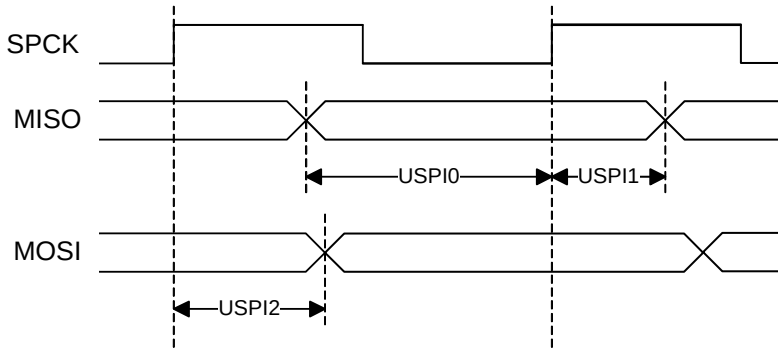


Figure 9-8. USART in SPI Master Mode with (CPOL= 0 and CPHA= 1) or (CPOL= 1 and CPHA= 0)

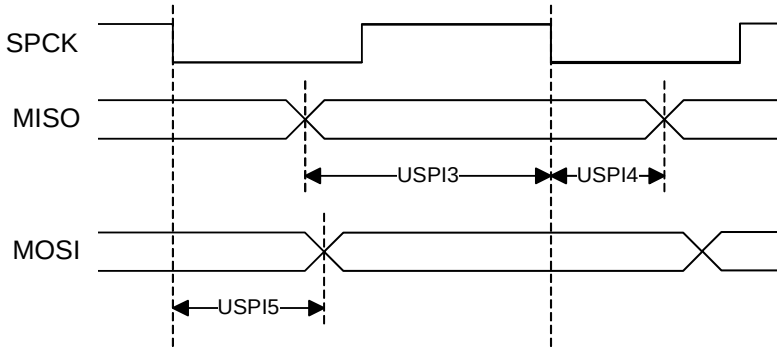


Figure 9-10. USART in SPI Slave Mode with (CPOL= CPHA= 0) or (CPOL= CPHA= 1)

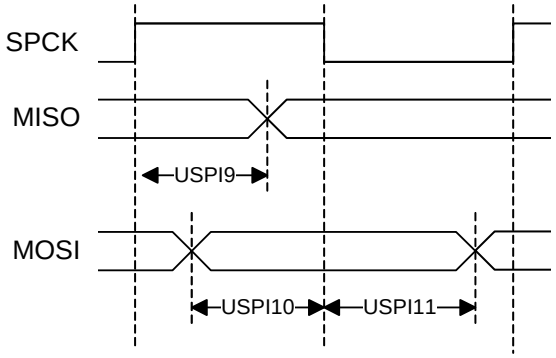


Figure 9-11. USART in SPI Slave Mode, NPCS Timing

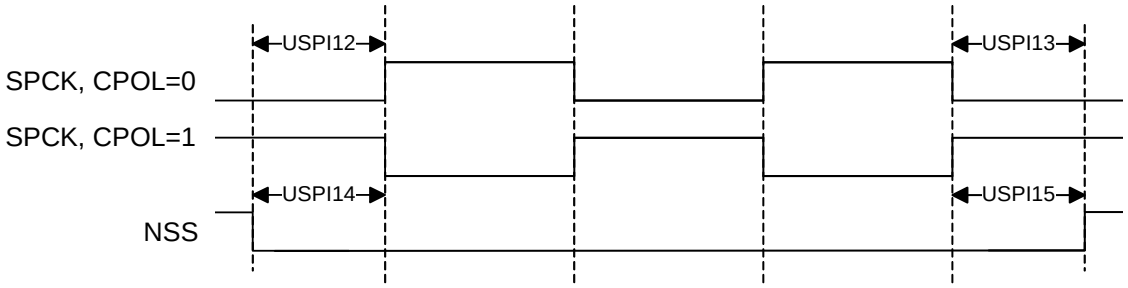


Table 9-58. USART0 in SPI mode Timing, Slave Mode[1]

Symbol	Parameter	Conditions	Min	Max	Units
USPI6	SPCK falling to MISO delay	V_{VDDIO} from 3.0V to 3.6V, maximum external capacitor = 40pF		740.67	ns
USPI7	MOSI setup time before SPCK rises		56.73 + t_{SAMPLE}[2] + t_{CLK_USART}		
USPI8	MOSI hold time after SPCK rises		45.18 -(t_{SAMPLE}[2] + t_{CLK_USART})		
USPI9	SPCK rising to MISO delay			670.18	
USPI10	MOSI setup time before SPCK falls		56.73 +(t_{SAMPLE}[2] + t_{CLK_USART})		
USPI11	MOSI hold time after SPCK falls		45.18 -(t_{SAMPLE}[2] + t_{CLK_USART})		
USPI12	NSS setup time before SPCK rises		688.71		
USPI13	NSS hold time after SPCK falls		-2.25		
USPI14	NSS setup time before SPCK falls		688.71		
USPI15	NSS hold time after SPCK rises		-2.25		

Figure 9-16. SPI Slave Mode, NPCS Timing

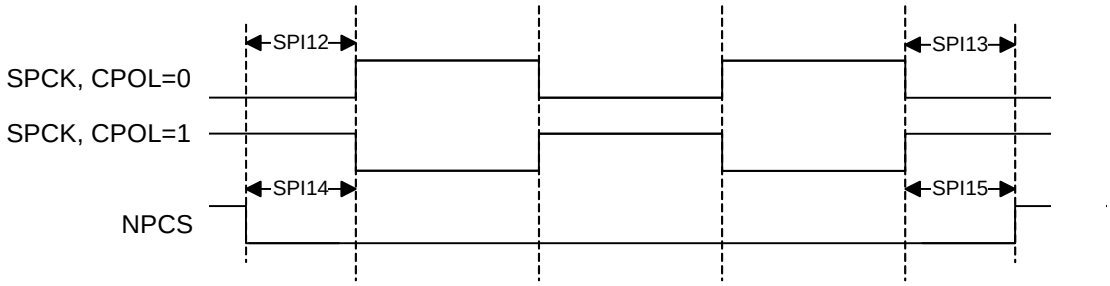


Table 9-63. SPI Timing, Slave Mode[1]

Symbol	Parameter	Conditions	Min	Max	Units
SPI6	SPCK falling to MISO delay	V_{VDDIO} from 2.85V to 3.6V, maximum external capacitor = 40pF	19	47	ns
SPI7	MOSI setup time before SPCK rises		0		
SPI8	MOSI hold time after SPCK rises		5.4		
SPI9	SPCK rising to MISO delay		19	46	
SPI10	MOSI setup time before SPCK falls		0		
SPI11	MOSI hold time after SPCK falls		5.3		
SPI12	NPCS setup time before SPCK rises		4		
SPI13	NPCS hold time after SPCK falls		2.5		
SPI14	NPCS setup time before SPCK falls		6		
SPI15	NPCS hold time after SPCK rises		1.1		

Note: 1. These values are based on simulation. These values are not covered by test limits in production.

Maximum SPI Frequency, Slave Input Mode

The maximum SPI slave input frequency is given by the following formula:

$$f_{SPCKMAX} = MIN(f_{CLKSPI}, \frac{1}{SPIn})$$

Where $SPIn$ is the MOSI setup and hold time, SPI7 + SPI8 or SPI10 + SPI11 depending on CPOL and NCPHA. f_{CLKSPI} is the maximum frequency of the CLK_SPI. Refer to the SPI chapter for a description of this clock.

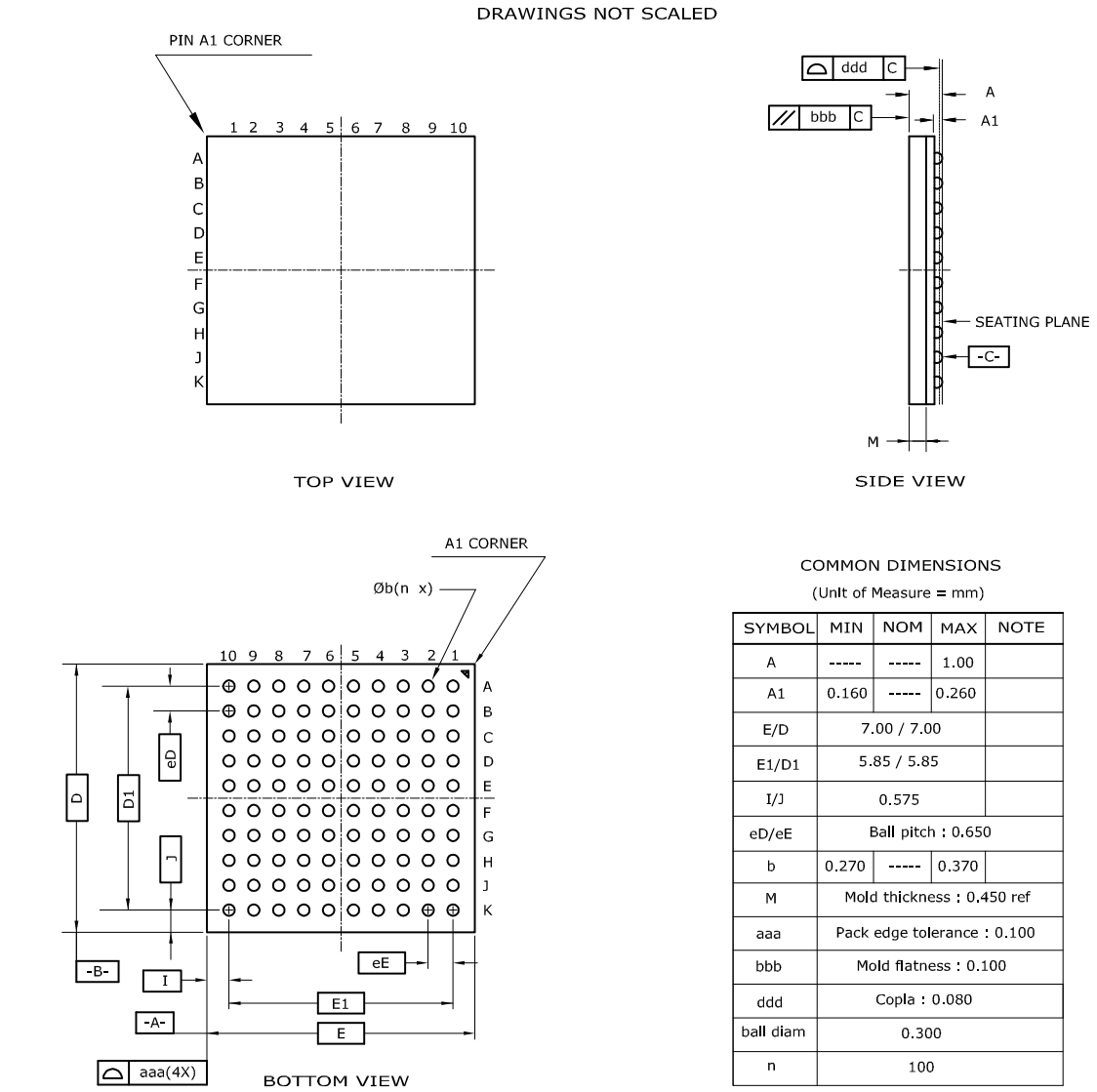
Maximum SPI Frequency, Slave Output Mode

The maximum SPI slave output frequency is given by the following formula:

$$f_{SPCKMAX} = MIN(f_{PINMAX}, \frac{1}{SPIn + t_{SETUP}})$$

10.2 Package Drawings

Figure 10-1. VFBGA-100 package drawing



COMMON DIMENSIONS

(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	-----	-----	1.00	
A1	0.160	-----	0.260	
E/D	7.00 / 7.00			
E1/D1	5.85 / 5.85			
I/J	0.575			
eD/eE	Ball pitch : 0.650			
b	0.270	-----	0.370	
M	Mold thickness : 0.450 ref			
aaa	Pack edge tolerance : 0.100			
bbb	Mold flatness : 0.100			
ddd	Copla : 0.080			
ball diam	0.300			
n	100			

Notes : 1. No JEDEC Drawing Reference.
2. Array as seen from the bottom of the package.
3. Dimension A includes stand-off height A1, package body thickness, and lid height, but does not include attached features.
4. Dimension b is measured at the maximum ball diameter, parallel to primary datum C.

Table 10-2. Device and Package Maximum Weight

120	mg

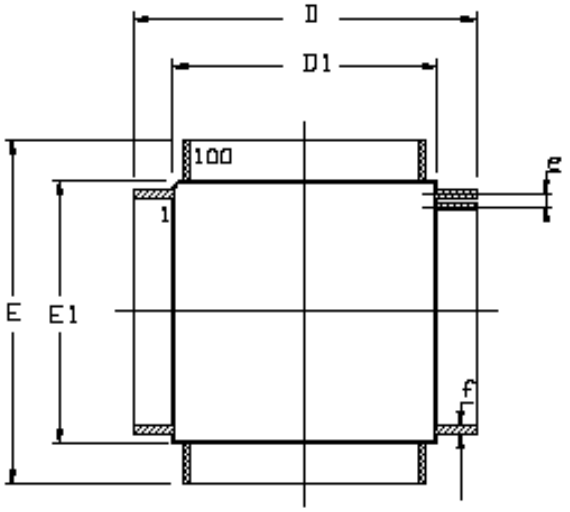
Table 10-3. Package Characteristics

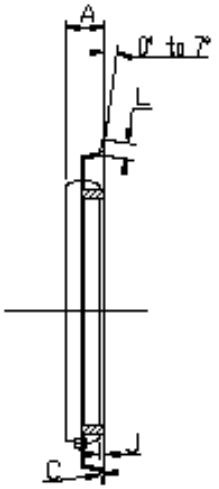
Moisture Sensitivity Level	MSL3

Table 10-4. Package Reference

JEDEC Drawing Reference	N/A
JESD97 Classification	E1

Figure 10-2. TQFP-100 Package Drawing





COMMON DIMENSIONS IN MM

SYMBOL	Min	Max	NOTES
A	----	1.20	
A1	0.95	1.05	
C	0.09	0.20	
D	16.00 BSC		
D1	14.00 BSC		
E	16.00 BSC		
E1	14.00 BSC		
J	0.05	0.15	
L	0.45	0.75	
e	0.50 BSC		
f	0.17	0.27	

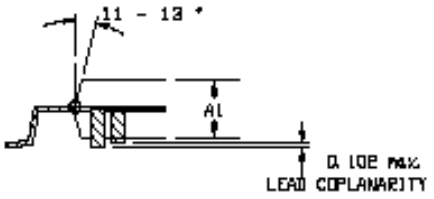


Table 10-5. Device and Package Maximum Weight

500	mg

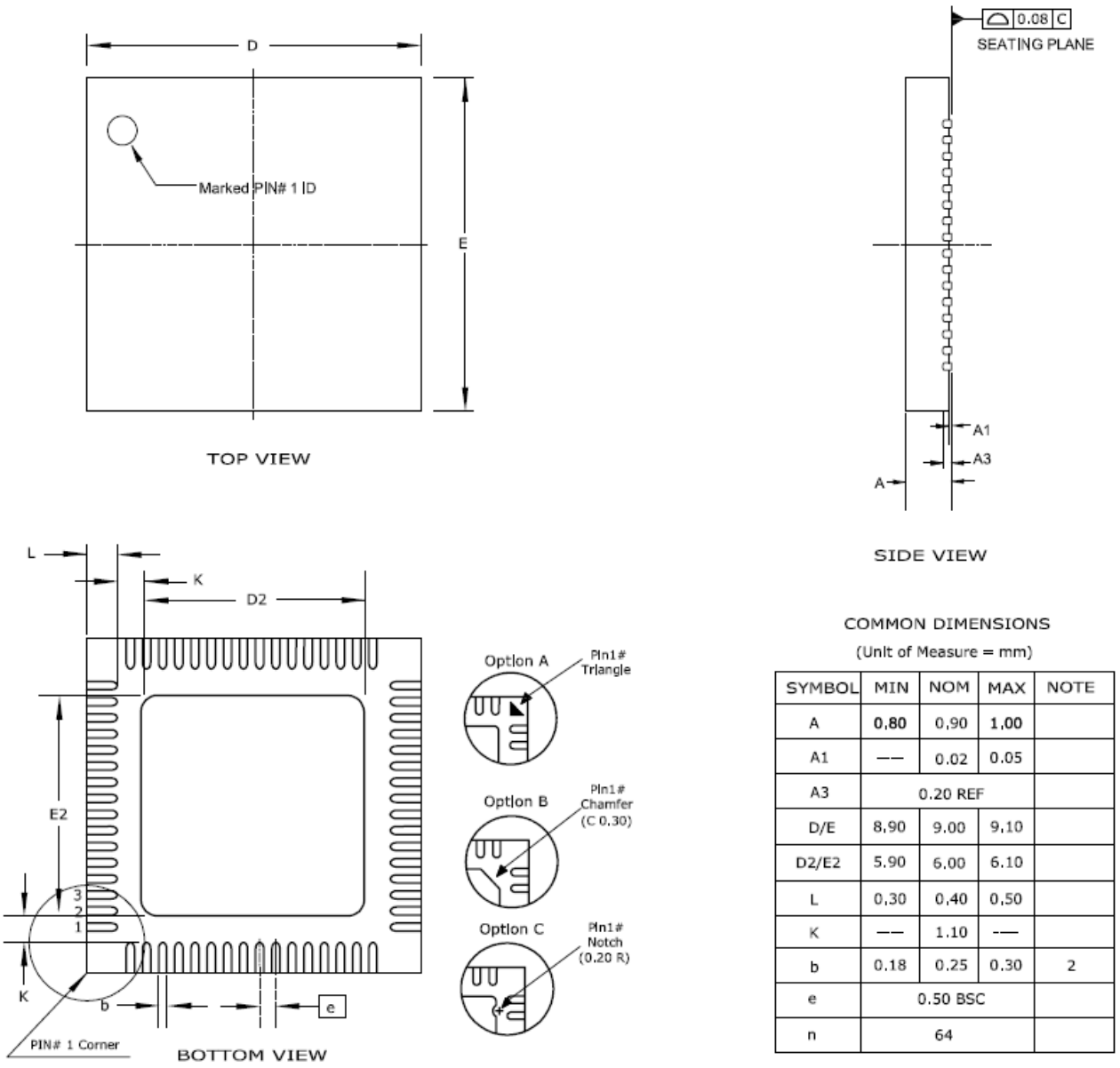
Table 10-6. Package Characteristics

Moisture Sensitivity Level	MSL3

Table 10-7. Package Reference

JEDEC Drawing Reference	MS-026
JESD97 Classification	E3

Figure 10-8. QFN-64 Package Drawing



COMMON DIMENSIONS

(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.80	0.90	1.00	
A1	—	0.02	0.05	
A3		0.20 REF		
D/E	8.90	9.00	9.10	
D2/E2	5.90	6.00	6.10	
L	0.30	0.40	0.50	
K	—	1.10	—	
b	0.18	0.25	0.30	2
e		0.50 BSC		
n		64		

Note: The exposed pad is not connected to anything internally, but should be soldered to ground to increase board level reliability.

Table 10-23. Device and Package Maximum Weight

200	mg

Table 10-24. Package Characteristics

Moisture Sensitivity Level	MSL3

Table 10-25. Package Reference

JEDEC Drawing Reference	MO-220
JESD97 Classification	E3

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